## 1<sup>st</sup> Order Metal-Insulator Transitions: Are They Universal in Manganites?

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The classic approach to the metal-insulator transition (MIT) is based on the overlap of wave functions as in the tight-binding model. Double exchange (DE) in manganites provides added tuning of the overlap by spin.

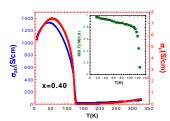
Continuous MITs: vanishing-number (e.g., a gap); or diverging-mass (e.g., Mott-Hubbard system V<sub>2</sub>O<sub>3</sub>) However Millis et al point out that DE is not enough--need localization mechanism above T<sub>C</sub>, e.g., polarons. 1st-order MITs: with Coulomb interaction (Mott); strong coupling to lattice, spin or orbital degrees of freedom

A continuous MIT is conventional wisdom in manganites: minimal hysteresis and scaling of magnetization in perovskite, La<sub>0.8</sub>Sr<sub>0.2</sub>MnO<sub>3</sub>.

## 1st-order MIT vs. H What have we learned? Bilayer manganites, La<sub>2-2x</sub>Sr<sub>1+2x</sub>Mn<sub>2</sub>O<sub>7</sub> Transport in La<sub>0.8</sub>Sr<sub>0.2</sub>MnO<sub>3</sub> fits to thermallyx~0.46 activated hopping, $\sigma \sim \exp(T_{hop}M(T)/M_sT)$ , without a concomitant MIT. 200 The AF stacking of FM Tokura and Lofland metallic bilayers leads to a La<sub>0.8</sub>Sr<sub>0.2</sub>MnO<sub>3</sub> continuous MIT in $\sigma_c(H_{ab})$ . 150 (mass-diverging OR 100 vanishing-number ??) 1st-order MIT vs. T 300 50 0.35 0.45 0.55 x~0.6 T(K) A-type AF H<sub>ab</sub>(Oe)

## Questions

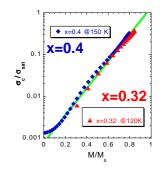
Is the 1st-order MIT versus T for x=0.6 universal for DE manganites (e.g., x-0.4)?



Can Anderson localization (due to random spin orientation and Hund's rule energy) explain the conductivity in PM insulator above T<sub>C</sub>?

> No sign of MIT above  $T_{\text{C}}$  in  $\sigma_{\text{ab}}$  or in  $\sigma_c(H){\sim}exp(T_{hop}M(H)/M_sT),$  even if polarons melted by a magnetic field: implies polarons alone are not the localization mechanism above T<sub>C</sub>

What is localization mechanism for x~0.46 in zero field? Is it gapped or Anderson localized?



## **Plans**

Data, in addition to conductivity/magnetization, ideally all on the same crystal

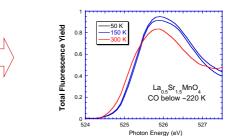
- tunneling (insulator gaps, metallic d.o.s.)
- polarization-dependent oxygen k-edge absorption (hybridized e<sub>a</sub> states)

Theory: cluster calculations M. Van Veenendaal (NIU)

To do:

- Establish tunneling and oxygen k-edge absorption for metallicity, gaps
- Identify MITs or insulator-insulator transitions: address if 1<sup>st</sup> or 2<sup>nd</sup> order
- Except for c-axis of x=0.3, are MITs always 1st-order in manganites?

Address whether a MIT occurs above T<sub>C</sub> in a sufficiently high magnetic field



In-plane e<sub>a</sub> states of single-layer manganite probed by xray absorption spectroscopy with ab-plane polarization.

Qing'An Li, K.E. Gray and J.F. Mitchell, Phys. Rev. B 67, 184426 (2003)





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